

GT60M303

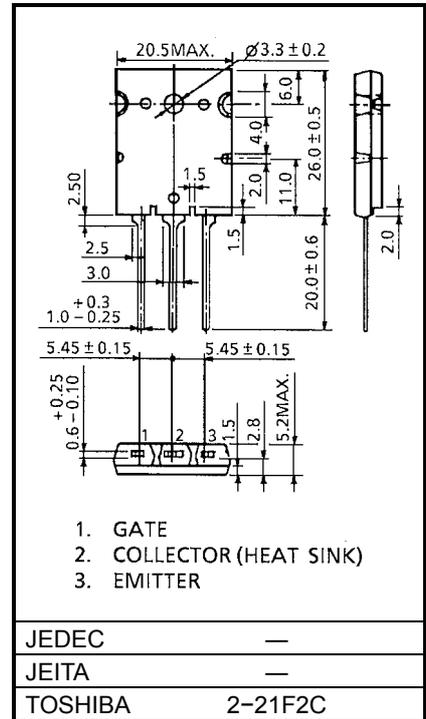
HIGH POWER SWITCHING APPLICATIONS

- The 4th Generation
- FRD Included Between Emitter and Collector
- Enhancement-Mode
- High Speed IGBT : $t_f = 0.25\mu s$ (TYP.)
FRD : $t_{rr} = 0.7\mu s$ (TYP.)
- Low Saturation Voltage : $V_{CE(sat)} = 2.1V$ (TYP.)

MAXIMUM RATINGS (Ta = 25°C)

CHARACTERISTIC		SYMBOL	RATING	UNIT
Collector-Emitter Voltage		V_{CES}	900	V
Gate-Emitter Voltage		V_{GES}	± 25	V
Collector Current	DC	I_C	60	A
	1ms	I_{CP}	120	
Emitter-Collector Forward Current	DC	I_{ECF}	15	A
	1ms	I_{ECFP}	120	
Collector Power Dissipation (Tc = 25°C)		P_C	170	W
Junction Temperature		T_j	150	°C
Storage Temperature Range		T_{stg}	-55~150	°C
Screw Torque		—	0.8	N·m

Unit: mm



EQUIVALENT CIRCUIT

